

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	Michael Heuken
Serial No. - Pending	Filing Date: November 17, 2003
Title of Application:	Method And Device For Depositing Layers
Confirmation No.	Art Unit:
Examiner	

Commissioner for Patents
Post Office Box 1450
Alexandria, VA 22313-1450

Information Disclosure Statement by Applicant

Dear Sir:

As a means of complying with the duty of disclosure set forth in 37 CFR §1.56, Applicant lists the following references (copies of the listed patents and papers enclosed).

U.S. Patent Documents				
Exam. Initials	Class/ Subclass.	Document No.	Date	Name
<i>SH</i>	118/733	4,976,217	12/1990	Frijlink
	118/715	4,991,540	2/1991	Jürgensen et al.
	437/110	5,162,256	11/1992	Jürgensen
	117/91	5,348,911	9/1994	Jürgensen et al.
	422/129	5,441,703	8/1995	Jürgensen
	118/715	5,453,124	9/1995	Moslehi et al.
	118/725	5,595,606	1/1997	Fujikawa et al.
	134/22.14	5,709,757	1/1998	Hatano et al.
	117/103	5,772,759	6/1998	Heime et al.
	118/715	6,086,677	7/2000	Umotoy et al.
<i>SH</i>	117/85	6,217,651	4/2001	Kashino et al.

9/27/04

Foreign Patent Documents			
Exam. Initials	Document No.	Date	Country
S	35 37 544 C1	5/1987	DE (with English abstract)
	WO 87/05700	9/1987	PCT
	36 08 783 C2	9/1987	DE (with English abstract)
	0 233 610 B1	8/1987	EP
	0 243 416 B1	4/1987	EP
	0 324 812 B1	7/1989	EP (with English abstract)
	0 428 673 B1	5/1991	EP (with English abstract)
	WO 91/20093	12/1991	PCT
	0 545 238 B1	6/1993	EP
	41 33 479 A1	9/1993	DE (with English abstract)
	42 32 504 A1	3/1994	DE (with English abstract)
	43 26 696 A1	2/1995	DE (with English abstract)
	43 26 697 A1	3/1995	DE (with English abstract)
	44 46 992 A1	7/1995	DE (with English abstract)
	195 22 574 A1	1/1996	DE (with English abstract)
	195 40 771 A1	7/1997	DE (with English abstract)
	198 13 523 A1	10/1999	DE (with English abstract)
S	WO 99/15710	4/1999	PCT

Other Documents	
Exam. Initials	Description (Author, Title, Date, Pages, etc)
S	Characterization of Epitaxial Semiconductor Growth, J.T. Zettler, Progression of Crystal Growth and Characterization, Vol 35, pp. 27-98, 1997

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